Title (en)

EXPOSURE METHOD, METHOD FOR FORMING PROJECTING AND RECESSED PATTERN, AND METHOD FOR MANUFACTURING OPTICAL ELEMENT

Title (de)

BELICHTUNGSVERFAHREN, VERFAHREN ZUR BILDUNG EINER PROJEKTION UND AUSGESPARTEN STRUKTUR UND VERFAHREN ZUR HERSTELLUNG EINES OPTISCHEN ELEMENTS

Title (fr)

PROCEDE D'EXPOSITION, PROCEDE DE FORMATION D'UN MOTIF A RENFORCEMENTS ET SAILLIES ET PROCEDE POUR FABRIQUER UN ELEMENT OPTIQUE

Publication

EP 1842100 A1 20071010 (EN)

Application

EP 06701442 A 20060124

Priority

- JP 2006301381 W 20060124
- JP 2005015799 A 20050124

Abstract (en)

[origin: WO2006078073A1] An exposure pattern having a line width of submicron size is simply formed by using an inexpensive and stable solid state laser or a gas laser as an exposure light source, and by using a photoresist for g-line or i-line. The exposure is performed by locally controlling a reaction time constant of the photosensitive material with beaming the laser beam on a predetermined portion of a layer of the photosensitive material having a predetermined thickness formed on the surface of a substrate W, with beam intensity and scanning rate of the laser beam being controlled.

IPC 8 full level

G03F 7/20 (2006.01); **G06K 15/00** (2006.01); G11B 7/26 (2006.01); H01L 21/027 (2006.01)

CPC (source: EP KR)

G03F 7/0002 (2013.01 - KR); **G03F 7/70383** (2013.01 - EP KR); **G03F 7/704** (2013.01 - EP KR); **G03F 7/70558** (2013.01 - EP KR)

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IS IT LI LT LU LV MC NL PL PT RO SE SI SK TR

DOCDB simple family (publication)

WO 2006078073 A1 20060727; CN 101133365 A 20080227; CN 101133365 B 20100811; EP 1842100 A1 20071010; EP 1842100 A4 20090429; KR 20070095362 A 20070928

DOCDB simple family (application)

JP 2006301381 W 20060124; CN 200680002960 A 20060124; EP 06701442 A 20060124; KR 20077016977 A 20070723